

C1  
would  
subsequently, separately forming a copper-diffusion stopper insulating film over said surface of said semiconductor substrate.--

Cancel claims 4 and 6.

Amend claim 18 as follows:

--18. (twice amended) A method of forming a semiconductor substrate having at least an interconnection made of a metal selected from the group consisting of copper, copper-based materials, and copper alloys, said method comprising the steps of:

C2  
carrying out a chemical mechanical polishing process for forming said at least interconnection in at least a groove in said semiconductor substrate;

subsequently removing metal contaminations from a surface of said semiconductor substrate and simultaneously or subsequently carrying out an anti-corrosion treatment by exposing said surface of said semiconductor substrate to a solution containing an anti-corrosive agent; and

subsequently, separately forming a copper-diffusion stopper insulating film over said surface of said semiconductor substrate.--

Cancel claims 20 and 22.

Add the following new claims:

C3  
--63. (new) A method of treating a surface of a semiconductor substrate, said surface of said semiconductor